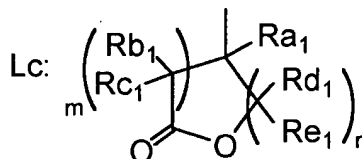


This listing of claims will replace all prior versions and listings of claims in the application:

1. (currently amended): A positive resist composition comprising:

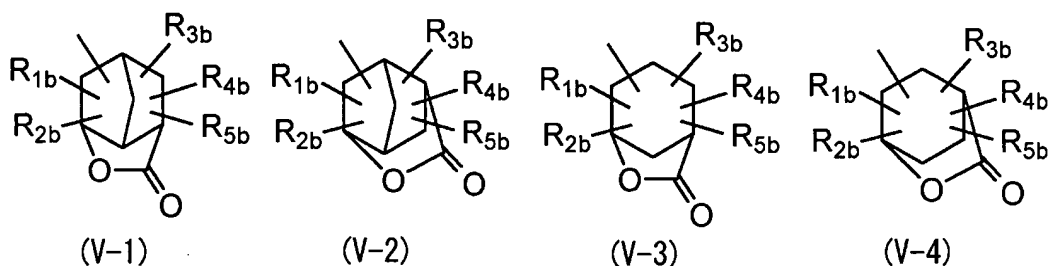
wherein the resin contains a repeating unit originated in an acrylic acid ester derivative in an amount of 50 to 100 mol% based on all repeating units and

(B) a compound capable of generating an acid upon irradiation with actinic rays or radiation, wherein the compound (B) contains a triaryl-sulfonium salt compound and a phenacylsulfonium salt compound, and

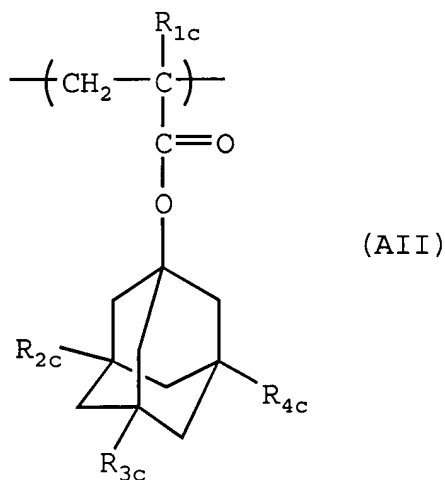
$$\text{-(CH}_2\text{-}\overset{\overset{\text{R}_{1a}}{|}}{\underset{\underset{\text{COO-W}_1\text{-Lc}}{|}}{\text{C}}}\text{)-} \quad \text{(IV)}$$


wherein R_{1a} represents a hydrogen atom or a methyl group, W_1 represents a single bond or a divalent linking group,

R_{a1} , R_{b1} , R_{c1} , R_{d1} and R_{e1} each independently represents a hydrogen atom or an alkyl group, m and n each independently represents an integer of 0 to 3, and $m+n$ is from 2 to 6;



wherein R_{1b} to R_{5b} each independently represents a hydrogen atom, an alkyl group, a cycloalkyl group or an alkenyl group, and two of R_{1b} to R_{5b} may be combined with each other to form a ring;



wherein R_{1c} represents a hydrogen atom or a methyl group, and R_{2c} to R_{4c} each independently represents a hydrogen atom, a hydroxyl group, an alkoxy group, an acyloxy group

or an alkyloxycarbonyloxy group, provided that one or two of R_{2c} to R_{4c} represents a hydroxyl group.

2. (original): The composition according to claim 1, wherein the resin (A) contains a repeating unit originated in an acrylic acid ester derivative in an amount of 60 to 100 mol% based on all repeating units.

3. (original): The positive resist composition according to claim 1, wherein in the resin (A), all repeating units are repeating units originated in an acrylic acid ester derivative.

4-5. (canceled).

6. (original): The composition according to claim 1, wherein the cyclic ketone is contained in an amount 20 to 70% by weight based on the total amount of the organic solvent (C).

7. (original): The composition according to claim 1, wherein the cyclic ketone is contained in an amount 30 to 60% by weight based on the total amount of the organic solvent (C).

8. (original): The composition according to claim 1, wherein the resin (A) contains a repeating unit having an alkali-soluble group protected by a 1-adamantyl-1-alkyl group.

9. (original): The composition according to claim 1, wherein the content of the repeating units represented by formula (IV) is from 20 to 70 mole % based on the total repeating units in the resin.

10. (original): The composition according to claim 9, wherein the content of the repeating units represented by formula (IV) is from 25 to 60 mole % based on the total repeating units in the resin.

11. (original): The composition according to claim 1, wherein the content of the repeating units represented by formulae (V-1) to (V-4) is from 20 to 70 mole % based on the total repeating units in the resin.

12. (original): The composition according to claim 11, wherein the content of the repeating units represented by formulae (V-1) to (V-4) is from 25 to 60 mole % based on the total repeating units in the resin.

13. (original): The composition according to claim 1, wherein the content of the repeating unit represented by formula (AII) is from 5 to 50 mole % based on the total repeating units in the resin.

14. (original): The composition according to claim 13, wherein the content of the repeating unit represented by formula (AII) is from 10 to 40 mole % based on the total repeating units in the resin.

15. (original): The composition according to claim 1, further comprising a nitrogen-containing basic compound.

16. (original): The composition according to claim 1, further comprising at least one of fluorine-based and/or silicon-based surfactants.

17. (original): A pattern formation method comprising steps of forming a resist film by using the positive resist composition claimed in claim 1, and exposing and developing said resist film.